

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.62	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.45	1.6	V	$I_C = 39A, V_{GE} = 15V$
		—	1.79	—		$I_C = 70A, V_{GE} = 15V$
		—	1.53	—		$I_C = 39A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-14	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	21	30	—	S	$V_{CE} = 100V, I_C = 39A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	2000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	190	290	nC	$I_C = 39A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	28	42		$V_{CC} = 400V, V_{GE} = 15V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	65	97		See Fig. 8
$t_{d(on)}$	Turn-On Delay Time	—	31	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	25	—		$I_C = 39A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	240	350		$V_{GE} = 15V, R_G = 5.0\Omega$
t_f	Fall Time	—	130	190		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	0.37	—	mJ	See Fig. 10, 11, 13, 14
E_{off}	Turn-Off Switching Loss	—	2.1	—		
E_{ts}	Total Switching Loss	—	2.47	3.0		
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$T_J = 150^\circ\text{C}$
t_r	Rise Time	—	24	—		$I_C = 39A, V_{CC} = 480V$
$t_{d(off)}$	Turn-Off Delay Time	—	390	—		$V_{GE} = 15V, R_G = 5.0\Omega$
t_f	Fall Time	—	230	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	5.0	—	mJ	See Fig. 13, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	4100	—	pF	$V_{GE} = 0V$
C_{oes}	Output Capacitance	—	250	—		$V_{CC} = 30V$
C_{res}	Reverse Transfer Capacitance	—	49	—		$f = 1.0MHz$

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 5.0\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.

- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

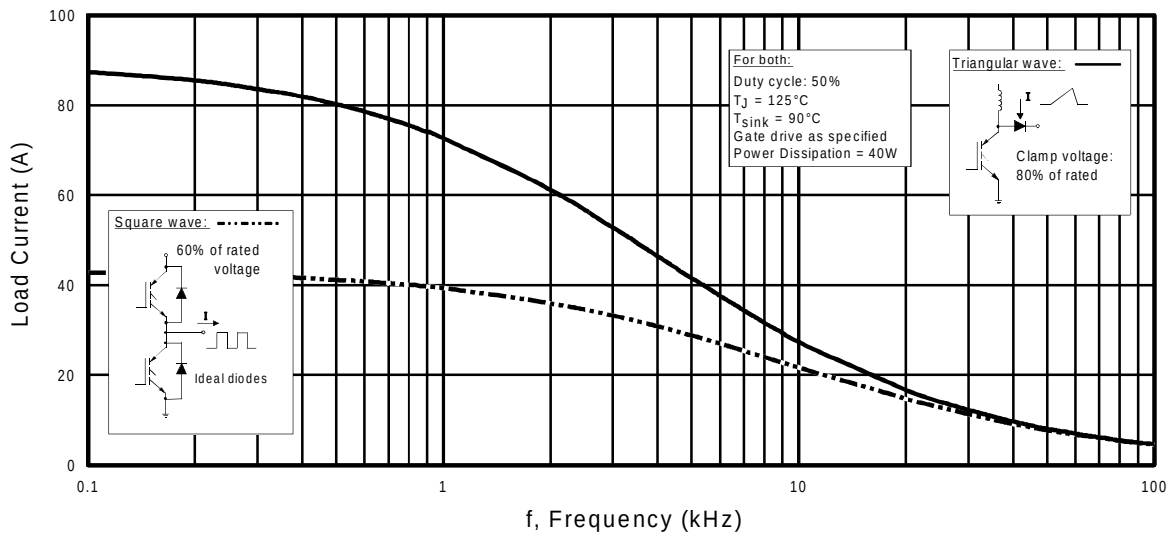


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{\text{RMS}}$ of fundamental; for triangular wave, $I = I_{\text{PK}}$)

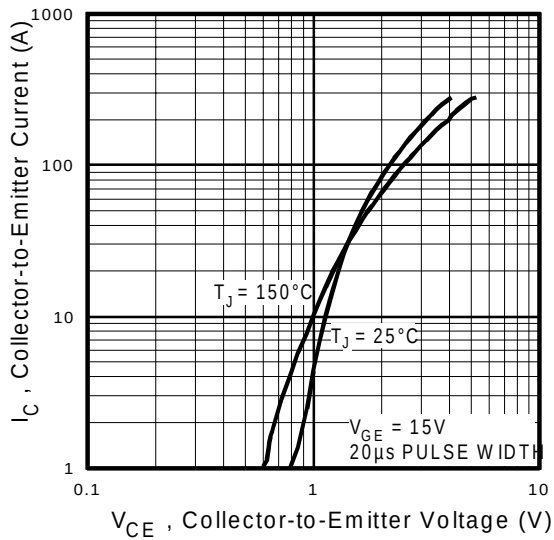


Fig. 2 - Typical Output Characteristics

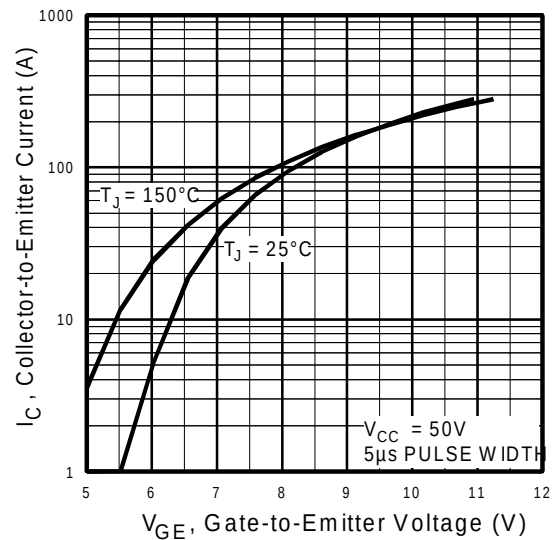


Fig. 3 - Typical Transfer Characteristics

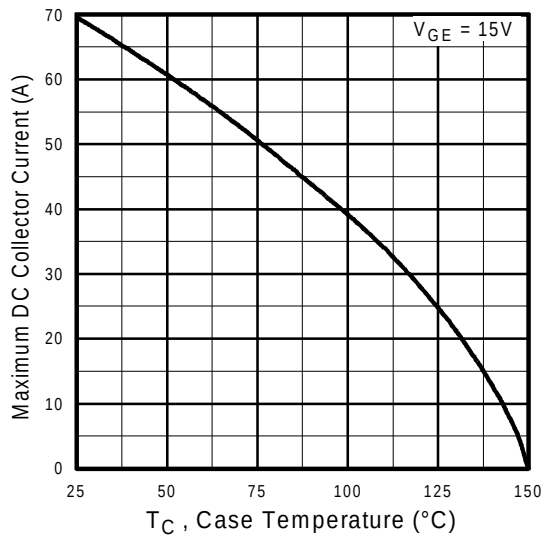


Fig. 4 - Maximum Collector Current vs. Case Temperature

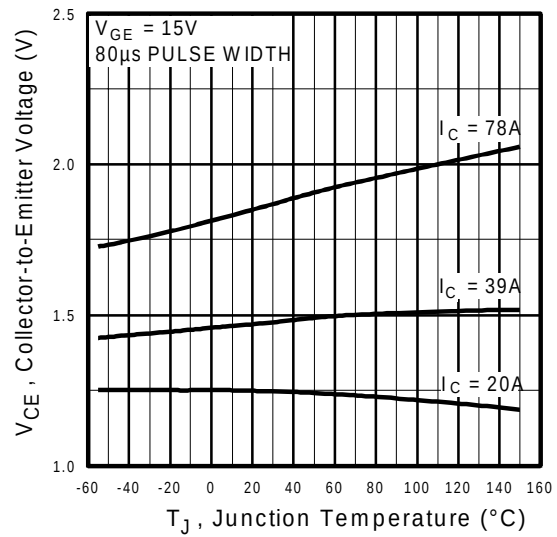


Fig. 5 - Collector-to-Emitter Voltage vs. Junction Temperature

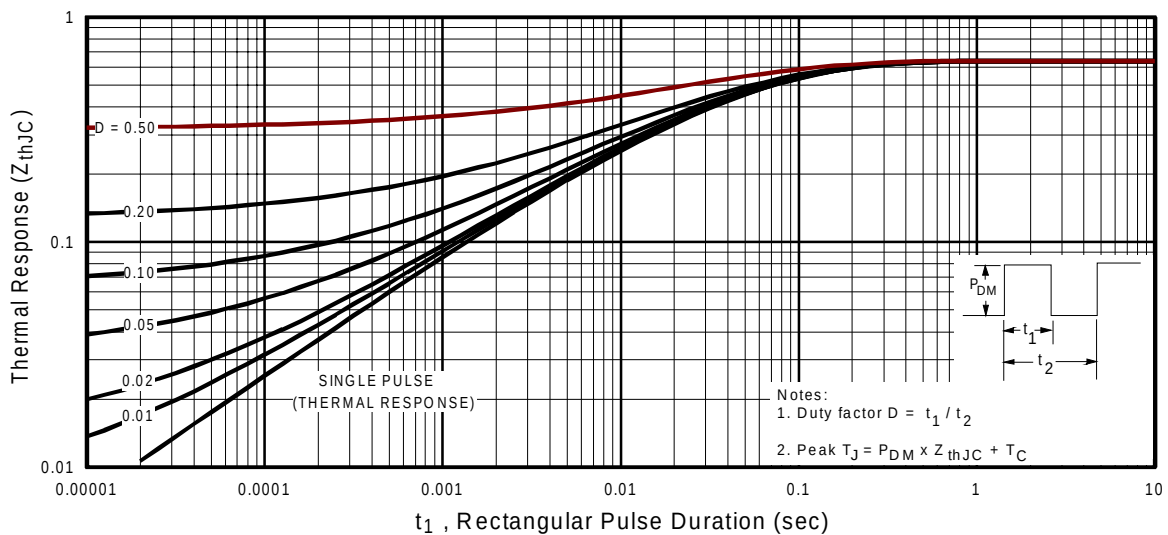


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

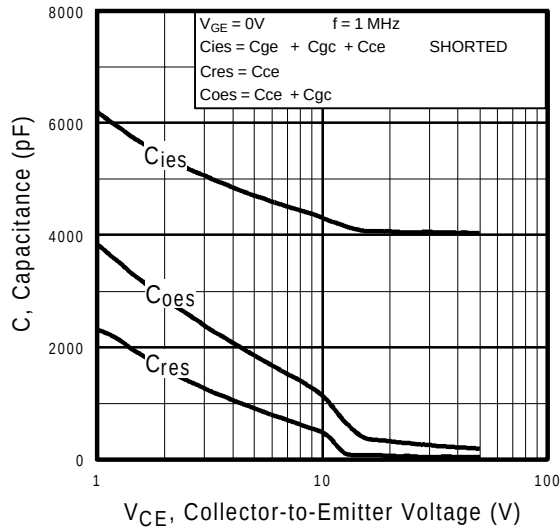


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

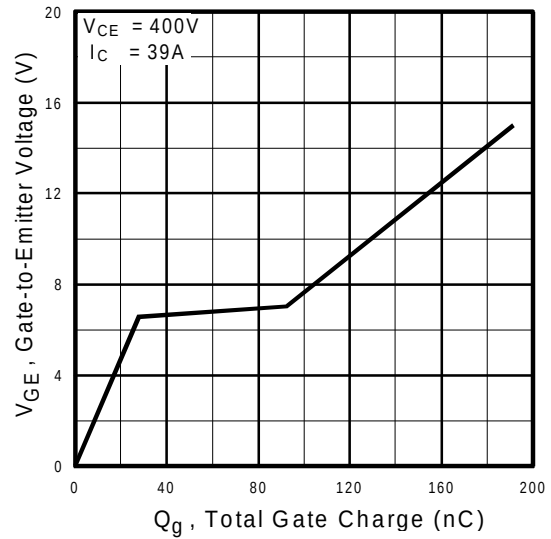


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

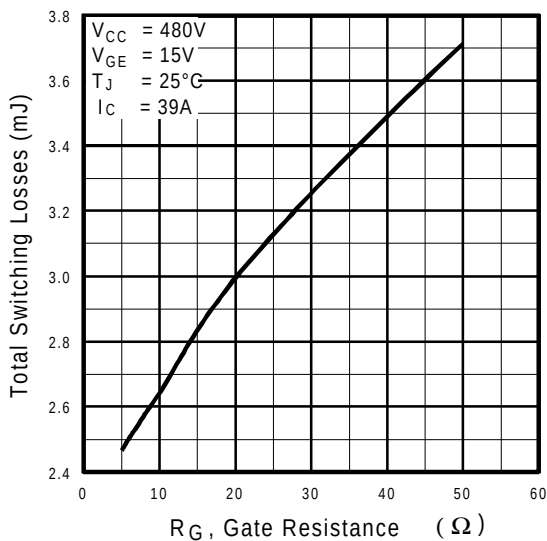


Fig. 9 - Typical Switching Losses vs. Gate Resistance

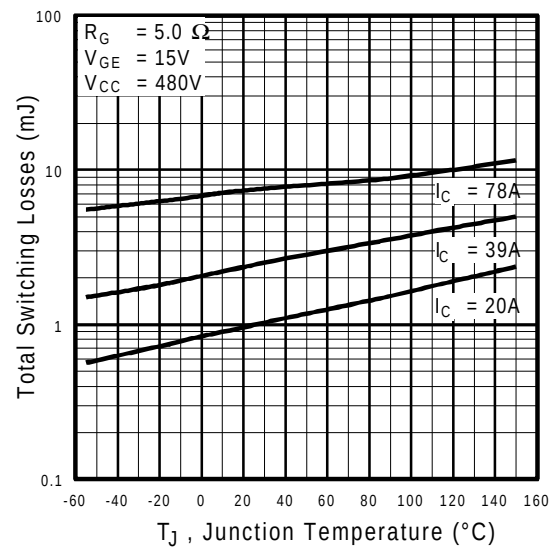


Fig. 10 - Typical Switching Losses vs. Junction Temperature

IRG4PC50F

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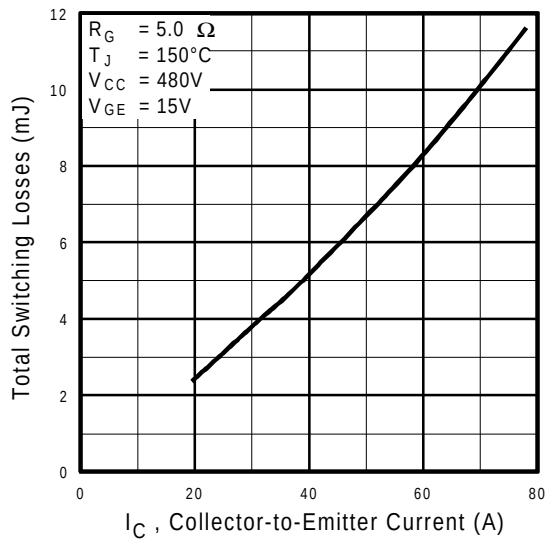


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

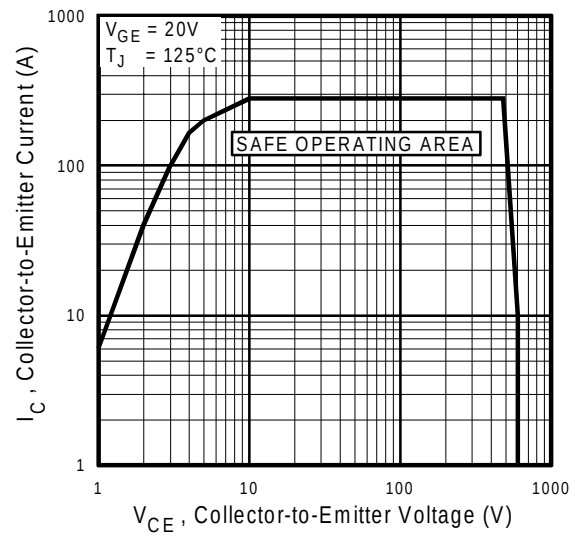


Fig. 12 - Turn-Off SOA

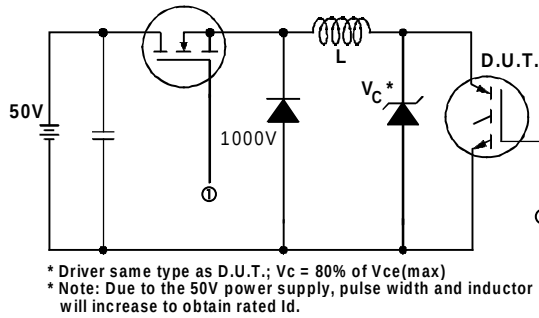


Fig. 13a - Clamped Inductive Load Test Circuit

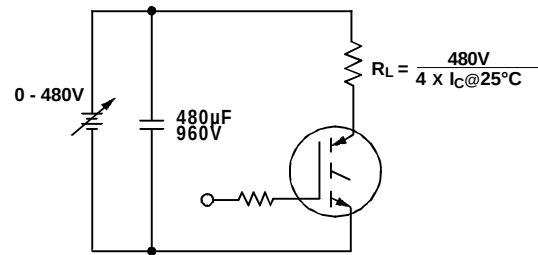


Fig. 13b - Pulsed Collector Current Test Circuit

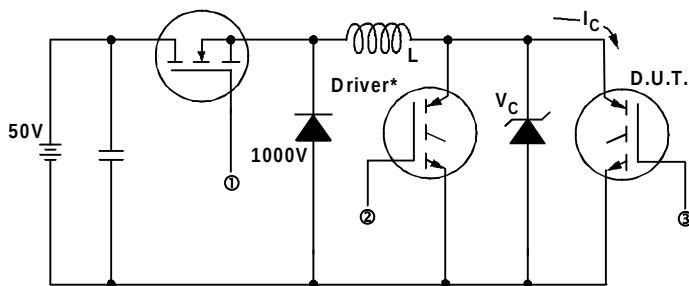


Fig. 14a - Switching Loss Test Circuit

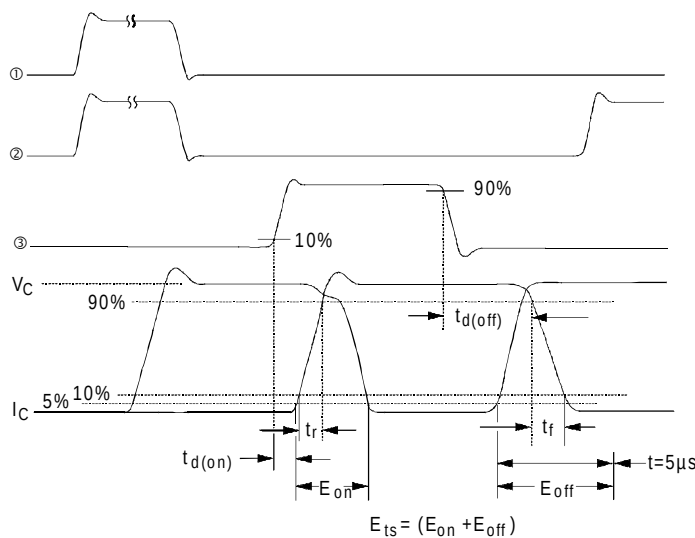


Fig. 14b - Switching Loss Waveforms

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Technical drawing of a TO-247AD transistor package showing top, side, and lead views with dimensions in millimeters and inches.

Top View Dimensions:

- Overall width: 15.90 (.626)
- Width between mounting holes: 15.30 (.602)
- Mounting hole diameter: $\varnothing 3.65 (.143)$
- Dimension A: $\varnothing 0.25 (.010) (M) D B (M)$
- Dimension B: 5.50 (.217)
- Dimension C: 2X $\varnothing 5.50 (.217)$
- Dimension D: 4.50 (.177)
- Dimension E: 14.80 (.583)
- Dimension F: 14.20 (.559)
- Dimension G: 2.40 (.094)
- Dimension H: 2.00 (.079)
- Dimension I: 2X 5.45 (.215)
- Dimension J: 3.40 (.133)
- Dimension K: 3.00 (.118)
- Dimension L: 1.40 (.056)
- Dimension M: 1.00 (.039)
- Dimension N: $\varnothing 0.25 (.010) (M) C A (S)$

Side View Dimensions:

- Overall height: 5.30 (.209)
- Dimension A: 4.70 (.185)
- Dimension B: 2.50 (.089)
- Dimension C: 1.50 (.059)
- Dimension D: 4
- Dimension E: 0.80 (.031)
- Dimension F: 0.40 (.016)
- Dimension G: 2.60 (.102)
- Dimension H: 2.20 (.087)

Lead Assignments:

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER
- 4 - COLLECTOR

NOTES:

- 1 DIMENSIONS & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 DIMENSIONS ARE SHOWN MILLIMETERS (INCHES).
- 4 CONFORMS TO JEDEC OUTLINE TO-247AC.

LEAD ASSIGNMENTS

*** LONGER LEADED (20mm) VERSION AVAILABLE (TO-247AD) TO ORDER ADD "E" SUFFIX TO PART NUMBER**

CONFORMS TO JEDEC OUTLINE TO-247AC (TO-3P)

Dimensions in Millimeters and (Inches)

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Visit us at www.irf.com for sales contact information.
Data and specifications subject to change without notice. 12/00

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>